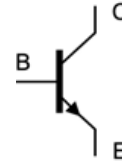


Features

- NPN transistor in Jedec TO-39 metal case.
- Designed for high speed switching application.
- Low leakage currents and low saturation voltage.



Schematic Diagram



TO-39

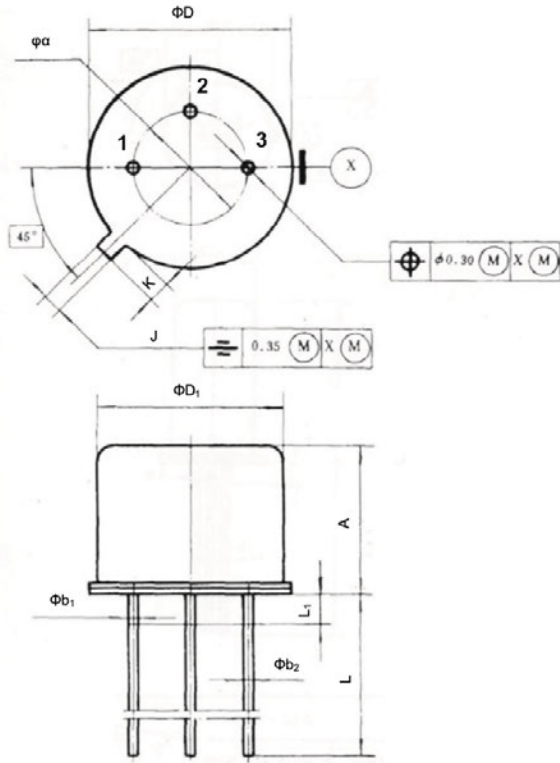
Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Collector-Emitter Voltage (I _B =0)	V _{CEO}	50	V
Collector-Base Voltage (I _E =0)	V _{CBO}	70	V
Emitter-Base Voltage (I _C =0)	V _{EBO}	6	V
Collector Current-Continuous	I _C	0.8	A
Collector Power Dissipation	P _{TOT}	0.9	W
Junction Temperature	T _J	-55 to +125	°C
Storage Temperature	T _{STG}	-55 to +150	°C

Electrical Characteristics (T_A=25°C unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Collector-Base Breakdown Voltage	V _{(BR)CEO}	I _C =10μA, I _E =0	50	-	-	V
Collector-Emitter Breakdown Voltage	V _{(BR)CBO}	I _C =10μA, I _E =0	70	-	-	V
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	I _E =10μA, I _C =0	6	-	-	V
Collector Cut-Off Current	I _{CBO}	V _{CB} =10V, I _E =0	-	-	100	nA
DC Current Gain	H _{FE}	V _{CE} =10V, I _C =10mA	50	-	240	-
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C =150mA, I _B =15mA	-	-	0.3	V
Base-Emitter Saturation Voltage	V _{BE(sat)}	I _C =150mA, I _B =15mA	-	-	1.2	V
Transition Frequency	F _T	I _C =20mA, V _{CE} =25V, F=100MHz	100	-	300	MHz

Package Outline Dimensions (TO-39)



Pin configuration:

- 1- Emitter
- 2- Base
- 3- Collector

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	6.100	6.600	0.240	0.260
ϕa	5.080 TYP		0.200 TYP	
Φb_1	-	1.010	-	0.040
Φb_2	0.407	0.508	0.016	0.020
ϕD	8.640	9.390	0.340	0.370
ΦD_1	8.010	8.500	0.315	0.335
J	0.712	0.863	0.028	0.034
K	0.740	1.140	0.029	0.045
L	12.50	25.00	0.492	0.984
L_1	-	1.270	-	0.050